Abstract

Method for polishing a semiconductor wafer with a strained-relaxed $Si_{1-x}Ge_x$ layer

The invention relates to a method for polishing a semiconductor wafer provided with a strain-relaxed layer of $Si_{1-x}Ge_x$, comprising a first step of a mechanical machining of the $Si_{1-x}Ge_x$ layer of the semiconductor wafer in a polishing machine using a polishing pad containing fixedly bonded abrasive materials having a particle size of 0.55 μm or less, and also a second step of a chemomechanical machining of the previously mechanically machined $Si_{1-x}Ge_x$ layer of the semiconductor wafer using a polishing pad and with supply of a polishing agent slurry containing abrasive materials.